

ABSTRACT OF THE INVENTION

The present invention is directed to a process for reclaiming for reuse a single crystal silicon wafer removed from an aborted semiconductor device fabrication process.

- 5 The process includes (a) subjecting the wafer to an oxide growth step to form an oxide layer having a thickness greater than 2 nanometers, (b) thinning the wafer by removing material from substantially the entire front surface to provide a thinned wafer having a thinned
- 10 precipitate free zone, and (c) polishing the front surface of the thinned wafer to a specular finish.

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